**July 2008** 



# FGH60N60SF 600V, 60A Field Stop IGBT

### **Features**

- High current capability
- Low saturation voltage:  $V_{CE(sat)} = 2.3V @ I_C = 60A$
- High input impedance •
- Fast switching •
- RoHS compliant •

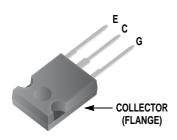
### Applications

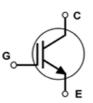
• Induction Heating, UPS, SMPS, PFC



## **General Description**

Using Novel Field Stop IGBT Technology, Fairchild's new series of Field Stop IGBTs offer the optimum performance for Induction Heating, UPS, SMPS and PFC applications where low conduction and switching losses are essential.





### **Absolute Maximum Ratings**

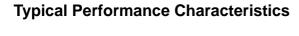
Symbol	Description		Ratings	Units
V <sub>CES</sub>	Collector to Emitter Voltage		600	V
V <sub>GES</sub>	Gate to Emitter Voltage		± 20	V
I <sub>C</sub>	Collector Current	@ T <sub>C</sub> = 25 <sup>o</sup> C	120	A
	Collector Current	@ T <sub>C</sub> = 100°C	60	A
I <sub>CM (1)</sub>	Pulsed Collector Current	@ T <sub>C</sub> = 25 <sup>o</sup> C	180	A
P <sub>D</sub>	Maximum Power Dissipation	@ T <sub>C</sub> = 25°C	378	W
	Maximum Power Dissipation	@ T <sub>C</sub> = 100°C	151	W
TJ	Operating Junction Temperature		-55 to +150	°C
T <sub>stg</sub>	Storage Temperature Range		-55 to +150	°C
TL	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

Notes: 1: Repetitive test, Pulse width limited by max. juntion temperature

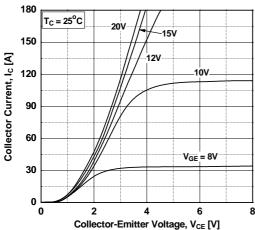
### **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction to Case	-	0.33	°C/W
R <sub>0JA</sub> Thermal Resistance, Junction to Ambient		-	40	°C/W

	lorking	Device	Dookogo	Packaging	Otype			x Qty
Device Marking Device   FGH60N60SF FGH60N60SF			Package Type		Qty per Tube		per Box	
FGH60h	NOUSF	FGH60N60SFTU	TO-247	Tube	30	)ea		-
Electric	al Chai	racteristics of the		5°C unless otherwise noted				
Symbol		Parameter	Test	Conditions	Min.	Тур.	Max.	Units
Off Charac	teristics							
BV <sub>CES</sub>	Collector	to Emitter Breakdown Voltage	$V_{GE} = 0V, I_{C}$	; = 250μΑ	600	-	-	V
ΔΒV <sub>CES</sub> ΔΤ <sub>J</sub>	Temperat Voltage	ure Coefficient of Breakdown	V <sub>GE</sub> = 0V, I <sub>C</sub>	$V_{GE} = 0V, I_{C} = 250 \mu A$		0.4	-	V/ºC
I <sub>CES</sub>	Collector	Cut-Off Current	$V_{CE} = V_{CES}$	, V <sub>GE</sub> = 0V	-	-	250	μΑ
I <sub>GES</sub>	G-E Leak	age Current	$V_{GE} = V_{GES}$	, V <sub>CE</sub> = 0V	-	-	±400	nA
On Charac	teristics		- <b>I</b>					
V <sub>GE(th)</sub>		shold Voltage	I <sub>C</sub> = 250μA,	$V_{CE} = V_{GE}$	4.0	5.0	6.5	V
			$I_{\rm C} = 60$ A, $V_{\rm G}$		-	2.3	2.9	V
V <sub>CE(sat)</sub>	Collector to Emitter Saturation Voltage			$I_{C} = 60A, V_{GE} = 15V,$ $T_{C} = 125^{\circ}C$		2.5	-	V
Dynamic C	haracteris	tics	1 -		-	1		Į
C <sub>ies</sub>	Input Cap			$V_{CE} = 30V, V_{GE} = 0V,$		2820	-	pF
C <sub>oes</sub>	Output Ca	apacitance				350	-	pF
C <sub>res</sub>	Reverse <sup>-</sup>	Transfer Capacitance	f = 1MHz		-	140	-	pF
			ł		-1	l		
Switching	-		1		-			
t <sub>d(on)</sub>		Delay Time	_			22 42	-	ns
t <sub>r</sub>	Rise Time	Delay Time			-	134	-	ns
t <sub>d(off)</sub> t <sub>f</sub>	Fall Time			$\label{eq:V_CC} \begin{array}{l} V_{CC} = 400 V, \ I_C = 60 A, \\ R_G = 5 \Omega, \ V_{GE} = 15 V, \\ \mbox{Inductive Load, } T_C = 25^o C \end{array}$		31	62	ns ns
ч E <sub>on</sub>		Switching Loss				1.79	-	mJ
E <sub>off</sub>		Switching Loss	_		-	0.67	-	mJ
E <sub>ts</sub>		ching Loss			-	2.46	-	mJ
t <sub>d(on)</sub>		Delay Time			-	22	-	ns
t <sub>r</sub>	Rise Time	; ;	1		-	44	-	ns
t <sub>d(off)</sub>	Turn-Off	Delay Time	V <sub>CC</sub> = 400V, I <sub>C</sub> = 60A,		-	144	-	ns
t <sub>f</sub>	Fall Time		$R_G = 5\Omega, V_G$	R <sub>G</sub> = 5Ω, V <sub>GE</sub> = 15V,	-	43	-	ns
E <sub>on</sub>	Turn-On S	Switching Loss	Inductive Lo	ad, T <sub>C</sub> = 125 <sup>o</sup> C	-	1.88	-	mJ
E <sub>off</sub>	Turn-Off S	Switching Loss			-	1.0	-	mJ
E <sub>ts</sub>	Total Swit	ching Loss			-	2.88	-	mJ
Qg	Total Gate	e Charge			-	198	-	nC
Q <sub>ge</sub>	Gate to E	mitter Charge	$V_{CE} = 400V,$	I <sub>C</sub> = 60A,	-	22	-	nC
Q <sub>gc</sub>	Cata ta C	ollector Charge	V <sub>GE</sub> = 15V		-	106		nC









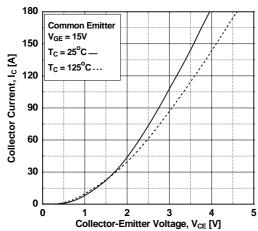
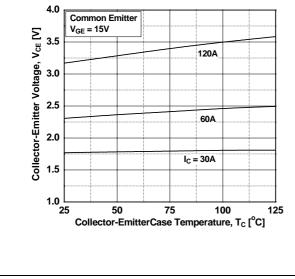
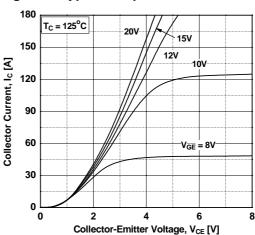


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level



**Figure 2. Typical Output Characteristics** 



**Figure 4. Transfer Characteristics** 

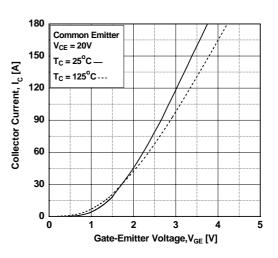
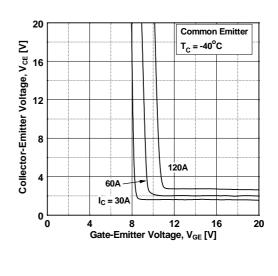
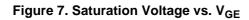
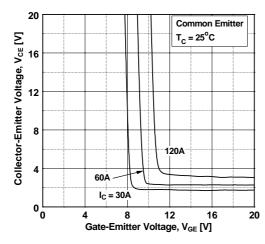


Figure 6. Saturation Voltage vs. V<sub>GE</sub>

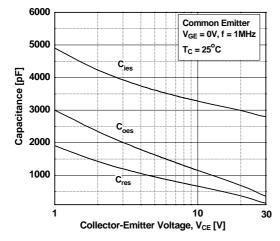


### **Typical Performance Characteristics**











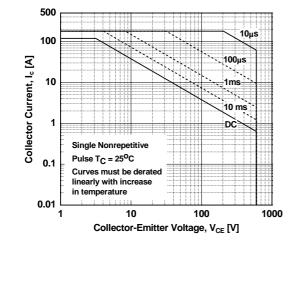


Figure 8. Saturation Voltage vs. V<sub>GE</sub>

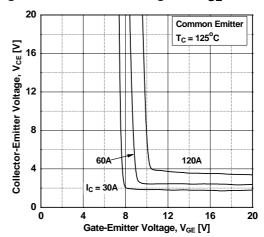


Figure 10. Gate charge Characteristics

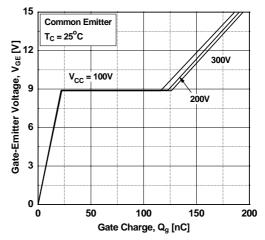
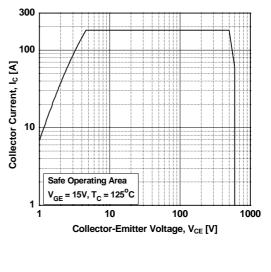
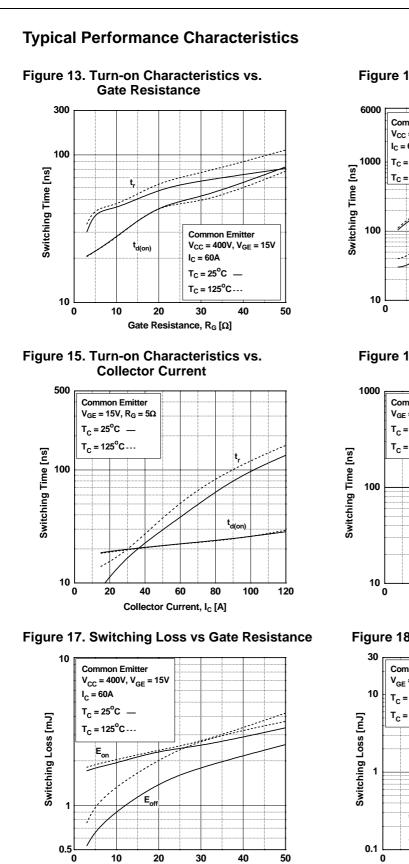
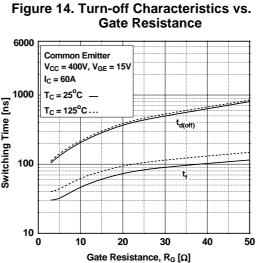


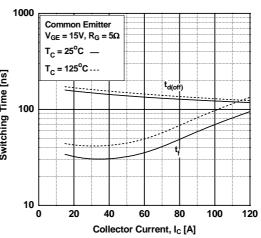
Figure 12. Turn off Switching SOA Characteristics



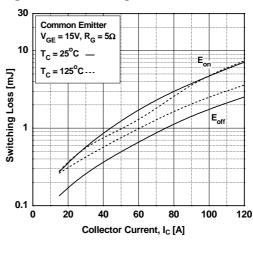












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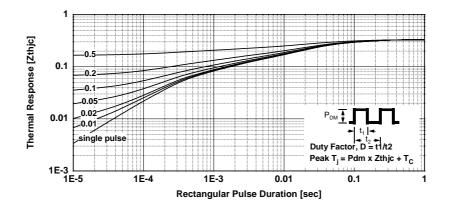
Gate Resistance, R<sub>G</sub> [Ω]

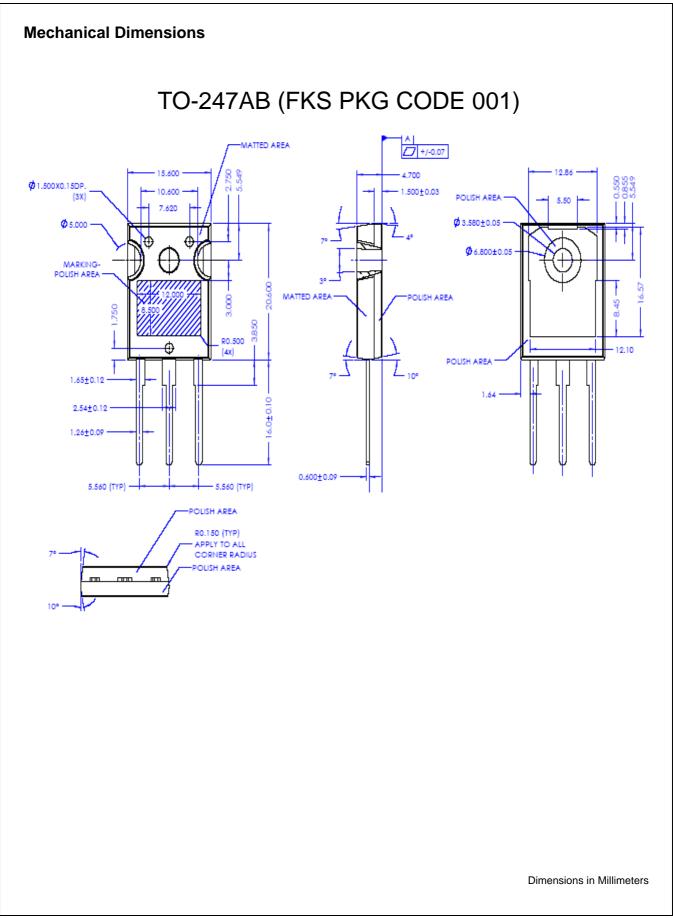
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FGH60N60SF 600V, 60A Field Stop IGBT

# Typical Performance Characteristics

## Figure 19. Transient Thermal Impedance of IGBT







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